MSKSEMI 美森科







TVC



TSS



MOV



GDT



PIFF

MMST2222A

Product specification

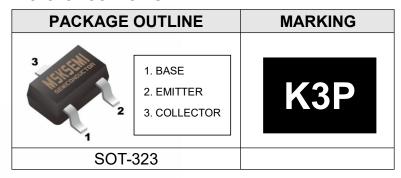




FEATURES

- Epitaxial planar die construction
- Complementary PNP Type available(MMST2907A)

Reference News



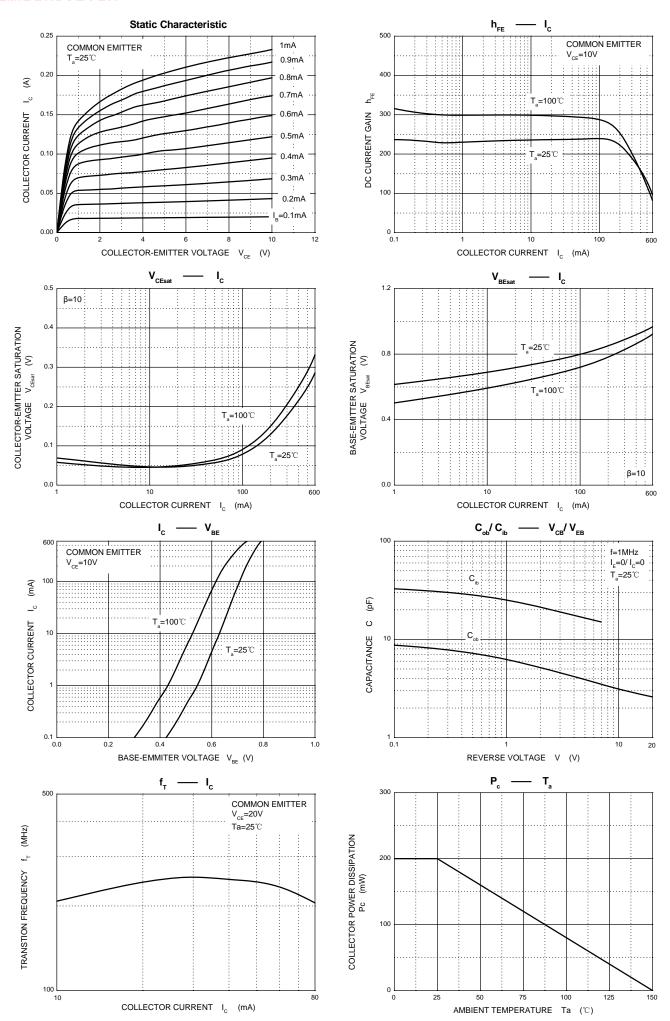
MAXIMUM RATINGS (Ta=25[°]C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	75	V
Vceo	Collector-Emitter Voltage	40	V
V _{EBO}	Emitter-Base Voltage	6	V
lc	Collector Current -Continuous	600	mA
Pc	Collector Dissipation	200	mW
T _J ,T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

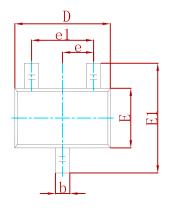
Parameter	Symbol	Test conditions	Min	Тур	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C = 10μA, I _E =0	75			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = 10mA, I _B =0	40			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =10μA, I _C =0	6			V
Collector cut-off current	Ісво	V _{CB} =70 V, I _E =0			100	nΑ
Collector cut-off current	Iceo	V _{CE} =35V , I _B =0			100	nΑ
Emitter cut-off current	I _{EBO}	V _{EB} = 3V , I _C =0			100	nA
	h _{FE(1)}	V _{CE} =10V, I _C =0.1mA	35			
	h _{FE(2)}	V _{CE} =10V, I _C = 1mA	50			
DC current gain	h _{FE(3)}	V _{CE} =10V, I _C = 10mA	75			
Do current gam	h _{FE(4)}	V _{CE} =10V, I _C = 150mA	100		300	
	h _{FE(5)}	V _{CE} =10V, I _C = 500mA	40			
	h _{FE(6)}	V _{CE} =1V, I _C = 150mA	35			
Collector-emitter saturation voltage	V _{CE(sat)}	I_{C} =500 mA, I_{B} = 50mA I_{C} =150 mA, I_{B} =15mA			1 0.3	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =500 mA, I _B = 50mA I _C =150 mA, I _B =15mA			2.0 1.2	V
Transition frequency	f⊤	V _{CE} =20V, I _C = 20mA f=100MHz	300			MHz
Output Capacitance	Cob	V _{CB} =10V, I _E = 0,f=1MHz			8	pF
Delay time	t _d	V _{CC} =30V, V _{BE(off)} =-0.5V			10	ns
Rise time	t _r	Ic=150mA , I _{B1} = 15mA			25	ns
Storage time	ts	V _{CC} =30V, I _C =150mA			225	ns
Fall time	t _f	I _{B1} =-I _{B2} =15mA			60	ns

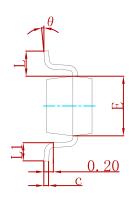


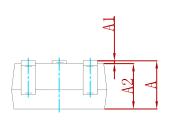




PACKAGEMECHANICALDATA

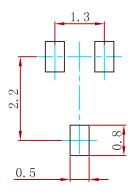






Symbol	Dimensions In Millimeters		Dimensions In Inches		
Syllibol	Min	Max	Min	Max	
Α	0.900	1.100	0.035	0.043	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.000	0.035	0.039	
b	0.200	0.400	0.008	0.016	
С	0.080	0.150	0.003	0.006	
D	2.000	2.200	0.079	0.087	
Е	1.150	1.350	0.045	0.053	
E1	2.150	2.450	0.085	0.096	
е	0.650 TYP		0.026 TYP		
e1	1.200	1.400	0.047	0.055	
L	0.525 REF		0.021 REF		
L1	0.260	0.460	0.010	0.018	
θ	0°	8°	0°	8°	

Suggested Pad Layout



Note:

- 1. Controlling dimension:in millimeters.
- 2.General tolerance:±0.05mm.
- 3. The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
MMST2222A	SOT-323	3000



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